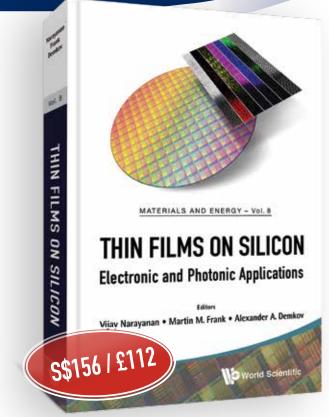
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350pp | Aug 2016 978-981-4740-47-0

Materials and Energy Vol.8

THIN FILMS ON SILICON Electronic and Photonic Applications

edited by

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The University of Texas at Austin, USA

This volume provides a broad overview of the fundamental materials science of thin films that use silicon as an active substrate or passive template, with an emphasis on opportunities and challenges for practical applications in electronics and photonics. It covers three materials classes on silicon: Semiconductors such as undoped and doped Si and SiGe, SiC,GaN, and III-V arsenides and phosphides; dielectrics including siliconnitride and high-k, low-k, and electro-optically active oxides; and metals, in particular silicide alloys. The impact of film growth and integration on physical, electrical, and optical properties, and ultimately device performance, is highlighted.

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Vijay Narayanan

Dr. Narayanan received his B.Tech. in Metallurgical Engineering from the Indian Institute of Technology,

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Dr. Narayanan was awarded an IBM Research Division Award for contributions to High- κ /Metal Gates in 2006 and was recognized as an IBM Master Inventor in 2007. He is an IEEE Senior Member and was elected a fellow of the American Physical Society in 2011. In addition, in recognition of his contributions to high- κ /metal gate technology, Dr. Narayanan received an IBM Corporate Award in 2013.



Martin Frank

Dr. Martin M. Frank is a Research Staff Member at IBM T. J. Watson Research Center in Yorktown Heights, NY. His research focuses on

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Dr. Frank has authored or co-authored more than 100 publications including multiple review articles and book chapters, has given more than 60 invited and contributed presentations, and holds more than 50 U.S. patents.



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Prof. Demkov is a professor of Physics at The University of Texas at Austin. He

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Prof. Demkov has published over 100 research papers and has been awarded seven U.S. patents. He has contributed to several books and edited one, entitled "Materials Fundamentals of Gate Dielectrics," and has also co-authored the 2005 edition of the International Technology Roadmap for Semiconductors (ITRS). In 2002-2004, he served as Associate Editor of the Journal of Vacuum Science and Technology B. He also served as Guest Editor for several issues of physica status solidi (b). Demkov received the NSF CAREER award, 2011 IBM Faculty Award, and is a Fellow of the American Physical Society.

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